

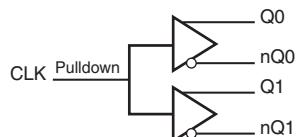
## GENERAL DESCRIPTION

The 85222-02 is a 1-to-2 LVC MOS / LV TTL-to-Differential HSTL translator. The 85222-02 has one single ended clock input. The single-ended clock input accepts LVC MOS or LV TTL input levels and translates them to HSTL levels. The small outline 8-pin SOIC package makes this device ideal for applications where space, high performance and low power are important.

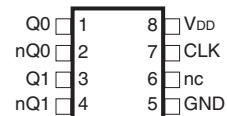
## FEATURES

- Two differential HSTL outputs
- One LVC MOS/LV TTL clock input
- CLK input can accept the following input levels: LVC MOS or LV TTL
- Maximum output frequency: 350MHz
- Part-to-part skew: 250ps (maximum)
- Propagation delay: 1.25ns (maximum)
- $V_{OH}$ : 1.4V (maximum)
- Output crossover voltage: 0.68V - 0.9V
- Full 3.3V operating supply voltage
- 0°C to 70°C ambient operating temperature
- Industrial temperature information available upon request
- Available in lead-free RoHS compliant package

## BLOCK DIAGRAM



## PIN ASSIGNMENT



**85222-02**  
**8-Lead SOIC**  
3.90mm x 4.92mm x 1.37mm body package  
**M Package**  
Top View

**TABLE 1. PIN DESCRIPTIONS**

| Number | Name     | Type   | Description                                      |                             |
|--------|----------|--------|--|-----------------------------|
| 1, 2   | Q0, nQ0  | Output | Differential output pair. HSTL interface levels. |                             |
| 3, 4   | Q1, nQ1  | Output | Differential output pair. HSTL interface levels. |                             |
| 5      | GND      | Power  | Power supply ground.                             |                             |
| 6      | nc       | Unused | No connect.                                      |                             |
| 7      | CLK      | Input  | Pulldown   | LVCMOS / LVTTL clock input. |
| 8      | $V_{dd}$ | Power  |  | Positive supply pin.        |

NOTE: *Pulldown* refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.

NOTE: Unused output pairs must be terminated.

**TABLE 2. PIN CHARACTERISTICS**

| Symbol         | Parameter               | Test Conditions | Minimum | Typical | Maximum | Units      |
|----------------|-------------------------|-----------------|---------|---------|---------|------------|
| $C_{in}$       | Input Capacitance       |                 |         | 4       |         | pF         |
| $R_{PULLDOWN}$ | Input Pulldown Resistor |                 |         | 51      |         | k $\Omega$ |

## ABSOLUTE MAXIMUM RATINGS

|  |                          |
|--|--------------------------|
| Supply Voltage, $V_{DD}$                 | 4.6V                     |
| Inputs, $V_i$                            | -0.5V to $V_{DD} + 0.5V$ |
| Outputs, $I_o$                           |                          |
| Continuous Current                       | 50mA                     |
| Surge Current                            | 100mA                    |
| Package Thermal Impedance, $\theta_{JA}$ | 112.7°C/W (0 lfpm)       |
| Storage Temperature, $T_{STG}$           | -65°C to 150°C           |

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

TABLE 3A. POWER SUPPLY DC CHARACTERISTICS,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = 0^\circ C$  TO  $70^\circ C$ 

| Symbol   | Parameter               | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|-------------------------|-----------------|---------|---------|---------|-------|
| $V_{DD}$ | Positive Supply Voltage |                 | 3.135   | 3.3     | 3.465   | V     |
| $I_{DD}$ | Power Supply Current    |                 |         |         | 50      | mA    |

TABLE 3B. LVCMOS / LVTTL DC CHARACTERISTICS,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = 0^\circ C$  TO  $70^\circ C$ 

| Symbol   | Parameter          | Test Conditions | Minimum                       | Typical | Maximum        | Units |
|----------|--------------------|-----------------|-------------------------------|---------|----------------|-------|
| $V_{IH}$ | Input High Voltage |                 | 2                             |         | $V_{DD} + 0.3$ | V     |
| $V_{IL}$ | Input Low Voltage  |                 | -0.3                          |         | 0.8            | V     |
| $I_{IH}$ | Input High Current | CLK             | $V_{DD} = V_{IN} = 3.465V$    |         | 150            | µA    |
| $I_{IL}$ | Input Low Current  | CLK             | $V_{DD} = 3.465, V_{IN} = 0V$ | -5      |                | µA    |

TABLE 3C. HSTL DC CHARACTERISTICS,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = 0^\circ C$  TO  $70^\circ C$ 

| Symbol      | Parameter                         | Test Conditions | Minimum | Typical | Maximum | Units |
|-------------|-----------------------------------|-----------------|---------|---------|---------|-------|
| $V_{OH}$    | Output High Voltage; NOTE 1       |                 | 1.0     |         | 1.4     | V     |
| $V_{OL}$    | Output Low Voltage; NOTE 1        |                 | 0       |         | 0.4     | V     |
| $V_{OX}$    | Output Crossover Voltage          |                 | 0.68    |         | 0.9     | V     |
| $V_{SWING}$ | Peak-to-Peak Output Voltage Swing |                 | 0.6     | 1.0     | 1.4     | V     |

NOTE 1: All outputs must be terminated with  $50\Omega$  to ground.

TABLE 4. AC CHARACTERISTICS,  $V_{DD} = 3.3V \pm 5\%$ ,  $T_A = 0^\circ C$  TO  $70^\circ C$ 

| Symbol      | Parameter                 | Test Conditions | Minimum | Typical | Maximum | Units |
|-------------|---------------------------|-----------------|---------|---------|---------|-------|
| $f_{MAX}$   | Output Frequency          |                 |         |         | 350     | MHz   |
| $t_{PD}$    | Propagation Delay; NOTE 1 |                 | 0.85    | 1.05    | 1.25    | ns    |
| $tsk(o)$    | Output Skew; NOTE 2, 3    |                 |         |         | 25      | ps    |
| $tsk(pp)$   | Part-to-Part Skew; NOTE 4 |                 |         |         | 250     | ps    |
| $t_r / t_f$ | Output Rise/Fall Time     | 20% to 80%      | 250     |         | 500     | ps    |
| odc         | Output Duty Cycle         | $f \le 250MHz$  | 45      |         | 55      | %     |
|             |                           | $f > 250MHz$    | 40      |         | 60      | %     |

All outputs must be terminated with  $50\Omega$  to ground.

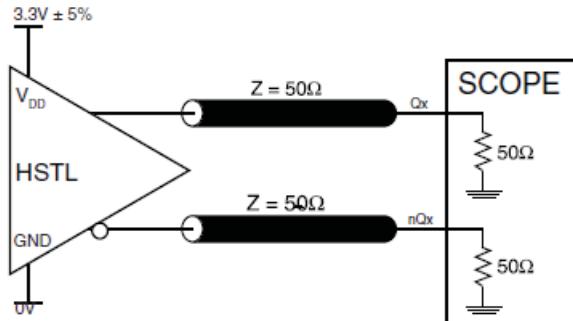
NOTE 1: Measured from  $V_{DD}/2$  of the input to the differential output crossing point.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

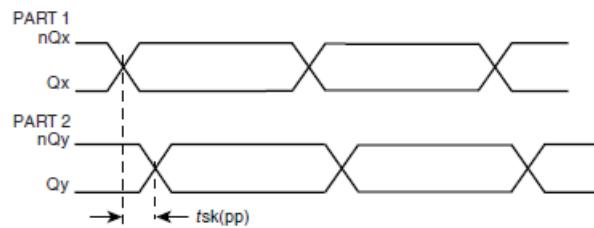
NOTE 4: Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross points.

# PARAMETER MEASUREMENT INFORMATION

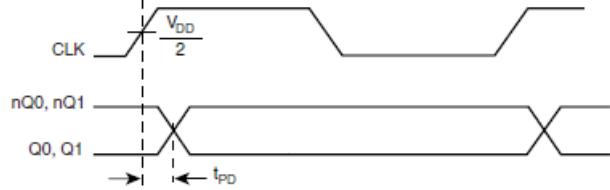
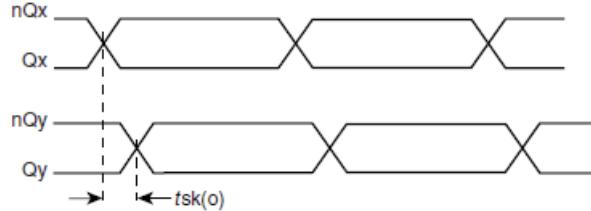


NOTE: All outputs must be terminated with  $50\Omega$  to ground.

## 3.3V CORE/3.3V OUTPUT LOAD AC TEST CIRCUIT

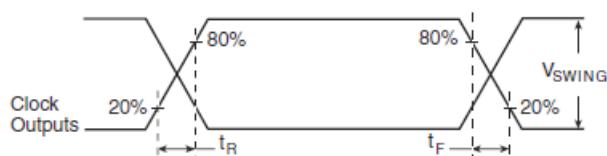
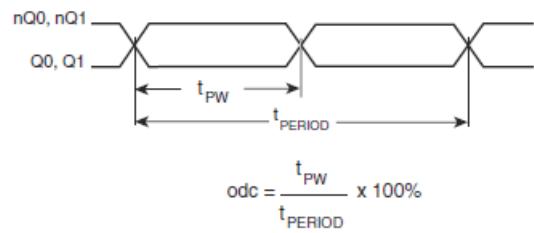


## PART-TO-PART SKEW



## OUTPUT SKEW

## PROPAGATION DELAY



## OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD

## OUTPUT RISE/FALL TIME

## APPLICATION INFORMATION

## RECOMMENDATIONS FOR UNUSED OUTPUT PINS

## OUTPUTS:

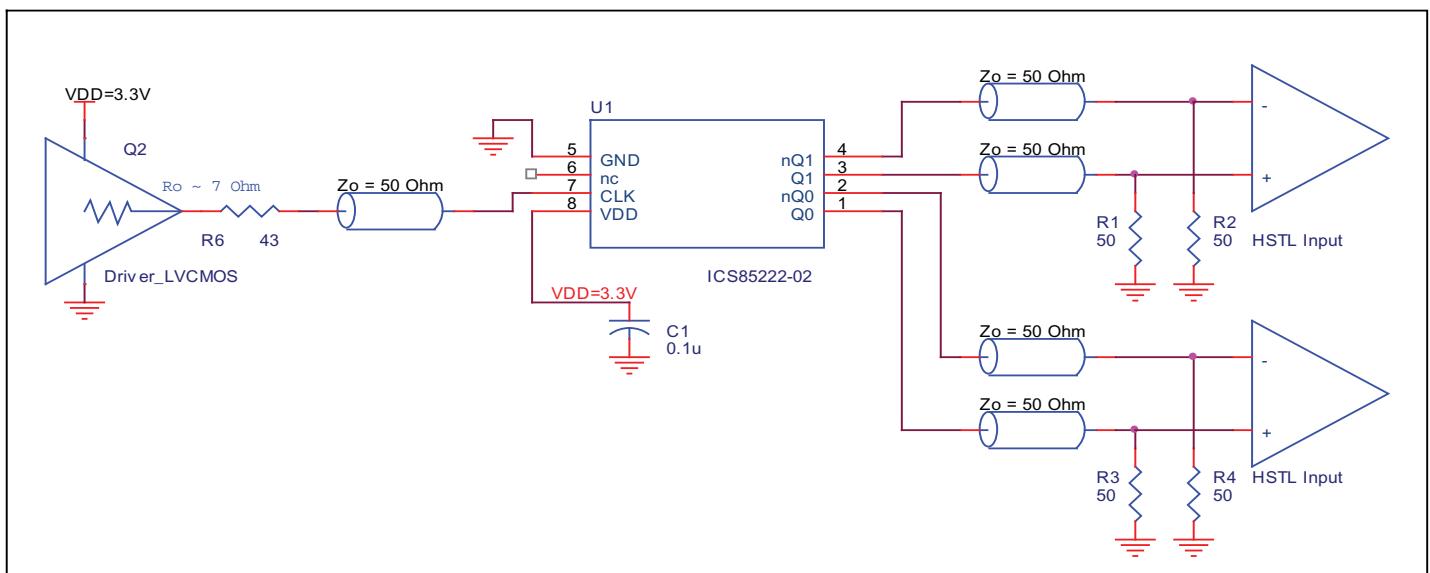
## HSTL OUTPUT

All outputs must be terminated with  $50\Omega$  to ground.

## SCHEMATIC EXAMPLE

Figure 2 shows a schematic example of 85222-02. In the example, the input is driven by a 7 ohm LVC MOS driver with a series termination. The decoupling capacitor should be physically located

near the power pin. For 85222-02, the unused output need to be terminated.



## FIGURE 2. 85222-02 HSTL BUFFER SCHEMATIC EXAMPLE

## POWER CONSIDERATIONS

This section provides information on power dissipation and junction temperature for the 85222-02. Equations and example calculations are also provided.

### 1. Power Dissipation.

The total power dissipation for the 85222-02 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for  $V_{DD} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

**NOTE:** Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)<sub>MAX</sub> =  $V_{DD,MAX} * I_{DD,MAX} = 3.465V * 50mA = 173.25mW$
- Power (outputs)<sub>MAX</sub> = **73.8mW/Loaded Output pair**  
If all outputs are loaded, the total power is  $2 * 82.3mW = 164.6mW$

**Total Power<sub>MAX</sub>** (3.465V, with all outputs switching) =  $173.25mW + 164.6mW = 337.86mW$

### 2. Junction Temperature.

Junction temperature,  $T_j$ , is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature for HiPerClockS™ devices is 125°C.

The equation for  $T_j$  is as follows:  $T_j = \theta_{JA} * P_{d\_total} + T_A$

$T_j$  = Junction Temperature

$\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

$P_{d\_total}$  = Total device power dissipation (example calculation is in Section 1 above)

$T_A$  = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming a moderate air flow of 200 linear feet per minute and a multi-layer board, the appropriate value is 103.3°C/W per Table 5 below. Therefore,  $T_j$  for an ambient temperature of 70°C with all outputs switching is:

$70^\circ C + 0.337W * 103.3^\circ C/W = 104.8^\circ C$ . This is below the limit of 125°C.

This calculation is only an example.  $T_j$  will obviously vary depending on the number of loaded outputs, supply voltage, air flow, and the type of board (single layer or multi-layer).

**TABLE 5. THERMAL RESISTANCE  $\theta_{JA}$  FOR 8-PIN SOIC, FORCED CONVECTION**

| <b><math>\theta_{JA}</math> by Velocity (Linear Feet per Minute)</b>  |           |            |            |
|---|-----------|------------|------------|
|   | <b>0</b>  | <b>200</b> | <b>500</b> |
| Single-Layer PCB, JEDEC Standard Test Boards  | 153.3°C/W | 128.5°C/W  | 115.5°C/W  |
| Multi-Layer PCB, JEDEC Standard Test Boards   | 112.7°C/W | 103.3°C/W  | 97.1°C/W   |
| <b>NOTE:</b> Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs. |           |            |            |

### 3. Calculations and Equations.

The purpose of this section is to derive the power dissipated into the load.

HSTL output driver circuit and termination are shown in *Figure 1*.

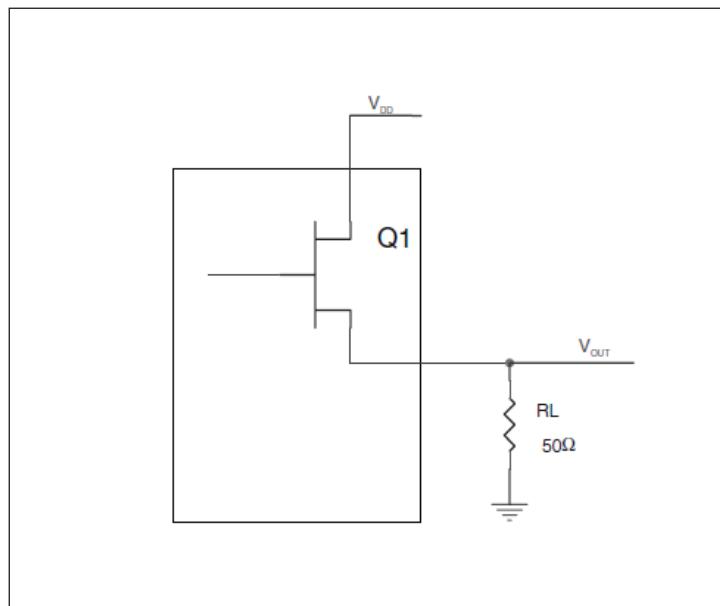


FIGURE 1. HSTL DRIVER CIRCUIT AND TERMINATION

To calculate worst case power dissipation into the load, use the following equations which assume a  $50\Omega$  load.

$P_{d,H}$  is power dissipation when the output drives high.

$P_{d,L}$  is the power dissipation when the output drives low.

$$P_{d,H} = (V_{_{OL,MAX}}/R_L) * (V_{_{DD,MAX}} - V_{_{OL,MAX}})$$

$$P_{d,L} = (V_{_{OL,MAX}}/R_L) * (V_{_{DD,MAX}} - V_{_{OL,MAX}})$$

$$P_{d,H} = (1.4V/50\Omega) * (3.465V - 1.4V) = 57.8mW$$

$$P_{d,L} = (0.4V/50\Omega) * (3.465V - 0.4V) = 24.52mW$$

$$\text{Total Power Dissipation per output pair} = P_{d,H} + P_{d,L} = 82.3mW$$

## RELIABILITY INFORMATION

TABLE 6.  $\theta_{JA}$  VS. AIR FLOW TABLE 8 LEAD SOIC

| <b><math>\theta_{JA}</math> by Velocity (Linear Feet per Minute)</b>  |           |            |            |
|---|-----------|------------|------------|
|   | <b>0</b>  | <b>200</b> | <b>500</b> |
| Single-Layer PCB, JEDEC Standard Test Boards  | 153.3°C/W | 128.5°C/W  | 115.5°C/W  |
| Multi-Layer PCB, JEDEC Standard Test Boards   | 112.7°C/W | 103.3°C/W  | 97.1°C/W   |
| <b>NOTE:</b> Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs. |           |            |            |

### TRANSISTOR COUNT

The transistor count for 85222-02 is: 411

## PACKAGE OUTLINE - M SUFFIX FOR 8 LEAD SOIC

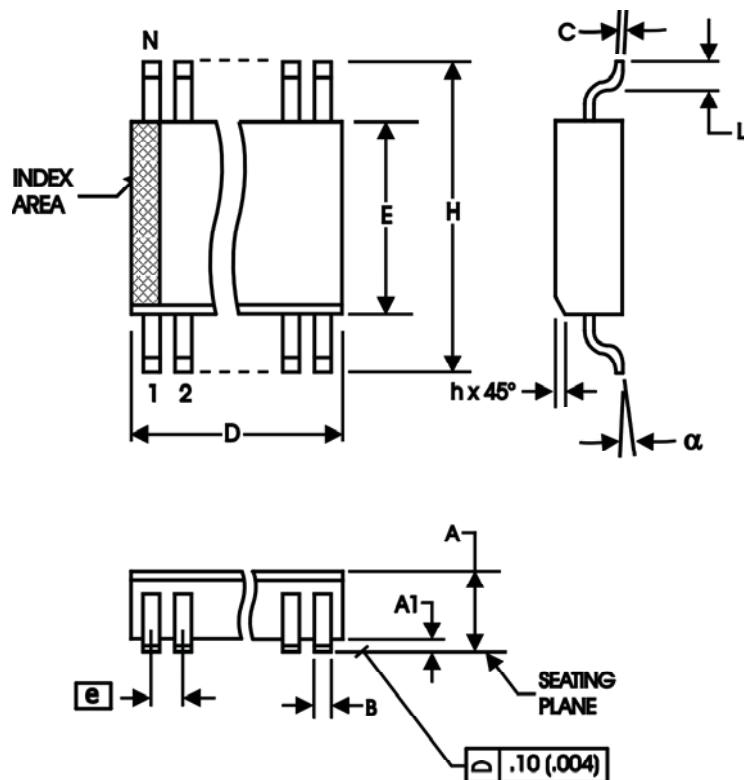


TABLE 7. PACKAGE DIMENSIONS

| SYMBOL   | Millimeters |         |
|----------|-------------|---------|
|          | MINIMUM     | MAXIMUM |
| N        | 8           |         |
| A        | 1.35        | 1.75    |
| A1       | 0.10        | 0.25    |
| B        | 0.33        | 0.51    |
| C        | 0.19        | 0.25    |
| D        | 4.80        | 5.00    |
| E        | 3.80        | 4.00    |
| e        | 1.27 BASIC  |         |
| H        | 5.80        | 6.20    |
| h        | 0.25        | 0.50    |
| L        | 0.40        | 1.27    |
| $\alpha$ | 0°          | 8°      |

Reference Document: JEDEC Publication 95, MS-012

**TABLE 8. ORDERING INFORMATION**

| Part/Order Number | Marking  | Package                 | Shipping Package | Temperature |
|-------------------|----------|-------------------------|------------------|-------------|
| ICS85222AM-02LF   | 5222A02L | 8 Lead "Lead-Free" SOIC | tube             | 0°C to 70°C |
| ICS85222AM-02LFT  | 5222A02L | 8 Lead "Lead-Free" SOIC | tape & reel      | 0°C to 70°C |

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

## REVISION HISTORY SHEET

| Rev | Table | Page     | Description of Change   | Date    |
|-----|-------|----------|---|---------|
| A   |       | 5<br>6-7 | Added <i>Schematic Example</i> .<br>Power Considerations - corrected power dissipation in calculations.   | 7/24/06 |
| B   | T1    | 1<br>2   | Updated Block Diagram with Pulldown for CLK.<br>Pin Description - changed pin 7 as Pulldown instead of Pullup. Changed note to reflect Pulldown.          |         |
|     | T2    | 2        | Pin Characteristics - changed Pullup Resistor to Pulldown.  | 9/12/07 |
|     | T3B   | 3        | LVCMOS DC Characteristics Table - changed $I_{IH}$ from 5 $\mu$ A max. to 150 $\mu$ A max. and changed $I_{IL}$ from -150 $\mu$ A min. to -5 $\mu$ A min. |         |
| B   | T8    | 10<br>1  | Ordering Information - removed leaded devices.<br>Features Section - removed reference to leaded devices.<br>Updated data sheet format.                   | 6/15/15 |



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